

Transistors

4V Drive Nch MOS FET

RSQ035N03

●Structure

Silicon N-channel MOS FET

●Features

- 1) Low On-resistance.
- 2) Space saving, small surface mount package (TSMT6).

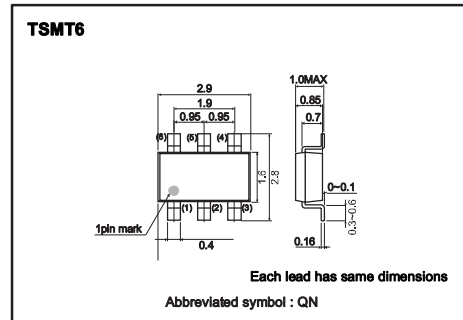
●Applications

Switching

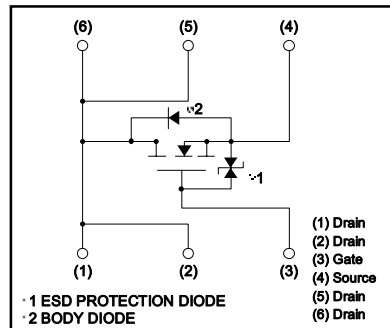
●Packaging specifications

Type	Package	Taping
	Code	TR
	Basic ordering unit (pieces)	3000
RSQ035N03		○

●External dimensions (Unit : mm)



●Inner circuit



●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit	
Drain-source voltage	V _{DSS}	30	V	
Gate-source voltage	V _{GSS}	20	V	
Drain current	Continuous	I _D	±3.5	A
	Pulsed	I _{DP} ^{∗1}	±14	A
Source current (Body diode)	Continuous	I _S	1.0	A
	Pulsed	I _{SP} ^{∗1}	14	A
Total power dissipation	P _D ^{∗2}	1.25	W	
Channel temperature	T _{ch}	150	°C	
Range of storage temperature	T _{stg}	-55 to +150	°C	

^{∗1} Pw:10μs, Duty cycle:1%

^{∗2} Mounted on a ceramic board

●Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to ambient	R _{th(ch-a)} [∗]	100	°C/W

[∗] Mounted on a ceramic board

Transistors

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	I_{GSS}	–	–	10	μA	$V_{GS}=20V, V_{DS}=0V$
Drain-source breakdown voltage	$V_{(BR)DSS}$	30	–	–	V	$I_D=1mA, V_{GS}=0V$
Zero gate voltage drain current	I_{DSS}	–	–	1	μA	$V_{DS}=30V, V_{GS}=0V$
Gate threshold voltage	$V_{GS(th)}$	1.0	–	2.5	V	$V_{DS}=10V, I_D=1mA$
Static drain-source on-state resistance	$R_{DS(on)}$	–	44	62	$m\Omega$	$I_D=3.5A, V_{GS}=10V$
		–	60	84	$m\Omega$	$I_D=3.5A, V_{GS}=4.5V$
		–	67	94	$m\Omega$	$I_D=3.5A, V_{GS}=4V$
Forward transfer admittance	$ Y_{fs} $	2.0	–	–	S	$V_{DS}=10V, I_D=3.5A$
Input capacitance	C_{iss}	–	290	–	pF	$V_{DS}=10V$
Output capacitance	C_{oss}	–	85	–	pF	$V_{GS}=0V$
Reverse transfer capacitance	C_{rss}	–	55	–	pF	$f=1MHz$
Turn-on delay time	$t_d(on)$	–	7	–	ns	$V_{DD}=15V$
Rise time	t_r	–	9	–	ns	$I_D=1.75A$
Turn-off delay time	$t_d(off)$	–	24	–	ns	$V_{GS}=10V$
Fall time	t_f	–	6	–	ns	$R_L=8.57\Omega$
Total gate charge	Q_g	–	5.3	7.4	nC	$V_{DD}=15V, V_{GS}=5V$
Gate-source charge	Q_{gs}	–	1.0	–	nC	$I_D=3.5A$
Gate-drain charge	Q_{gd}	–	1.4	–	nC	$R_L=4.29\Omega, R_G=10\Omega$

Pulsed

●Body diode characteristics (Source-drain) (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_{SD}	–	–	1.2	V	$I_S=1.0A, V_{GS}=0V$

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